



Three-wire Serial EEPROM

1K bits (128 X 8 or 64 X 16)



► Low-voltage Operation

- 1.8 (VCC = 1.8V to 5.5V)

►Three-wire Serial Interface

▶2 MHz Clock Rate (5V) Compatibility

► Self-timed Write Cycle (5 ms max)

► High-reliability

- Endurance: 1 Million Write Cycles

- Data Retention: 100 Years

▶8-lead PDIP/SOP/MSOP/TSSOP, 8-pad DFN packages

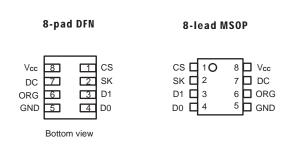
■ General Description

The K93C46 provides 1024 bits of serial electrically erasable programmable read only memory (EEPROM) organized as 64 words of 16 bits each, when the ORG pin is connected to VCC and 128 words of 8 bits each when it is tied to ground. The K93C46 is available in space-saving 8-lead PDIP, 8-lead SOP, 8-lead TSSOP, 8-lead MSOP, and 8-pad DFN packages. The K93C46 is enabled through the Chip Select pin (CS), and accessed via a 3-wire serial interface consisting of Data Input (DI), Data Output (DO), and Shift Clock (SK) signals. Upon receiving a Read instruction at DI, the address is decoded and the data is clocked out serially on the data output pin DO. The WRITE cycle is completely self-timed and no separate erase cycle is required before write. The Write cycle is only enabled when it is in the Erase/Write Enable state. When CS is brought "high" following the initiation of a write cycle, the DO pin outputs the Ready/Busy status.

■ Pin Configuration

► Table 1: Pin Configuration

Pin Name	Founctions
CS	Chip Select
SK	Serial Data Clock
DI	Serial Data Input
DO	Serial Data Output
GND	Ground
Vcc	Power Supply
ORG	Internal Organization
DC	Don't Connect



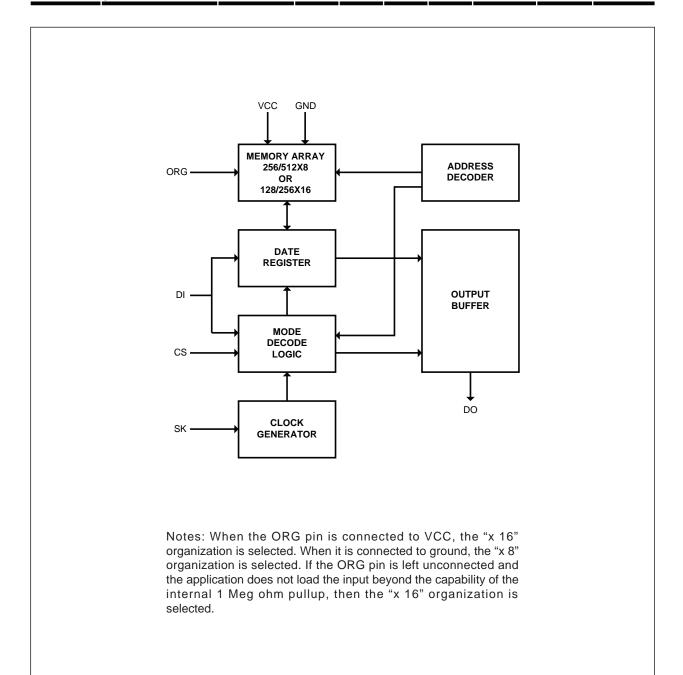


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Three-wire Serial EEPROM 1K bits (128 X 8 or 64 X 16)



■ Block Diagram



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1K bits (128 X 8 or 64 X 16)



■ Function Descriptions

The K93C46 is accessed via a simple and versatile three-wire serial communication interface. Device operation is controlled by seven instructions issued by the host processor. A valid instruction starts with a rising edge of CS and consists of a start bit (logic"1") followed by the appropriate op code and the desired memory address location.

► Table 2: Instruction Set for the K93C56/66

Instruction	SB	OP Code	Add	lress	Data		Comments
IIISHUCHOII	SD	OF Code	х8	x16	x8	x16	Comments
READ	1	10	A8 - A0	A7 - A0			Reads data stored in memory, at specified address
EWEN	1	00	11XXXXXXX	11XXXXXX			Write enable must precede all programming modes
ERASE	1	11	A8 - A0	A7 - A0			Erase memory location An - A0
WRITE	1	01	A8 - A0	A7 - A0	D7 - D0	D15 - D0	Writes memory location An - A0
ERAL	1	00	10XXXXXXX	10XXXXXX			Erases all memory locations. Valid only at VCC = 4.5V to 5.5V
WRAL	1	00	01XXXXXXX	01XXXXXX	D7 - D0	D15 - D0	Writes all memory locations. Valid only at VCC = 4.5V to 5.5V
EWDS	1	00	00XXXXXXX	00XXXXXX			Disables all programming instructions

Notes: The X's in the address field represent don't care values and must be clocked.

READ (**READ**): The Read (READ) instruction contains the address code for the memory location to be read. After the instruction and address are decoded, data from the selected memory location is available at the serial output pin DO. Output data changes are synchronized with the rising edges of serial clock SK. It should be noted that a dummy bit (logic "0") precedes the 8- or 16-bit data output string.

ERASE/WRITE (EWEN): To assure data integrity, the part automatically goes into the Erase/Write Disable (EWDS) state when power is first applied. An Erase/Write Enable(EWEN) instruction must be executed first before any programming instructions can be carried out. Please note that once in the EWEN state, programming remains enabled until an EWDS instruction is executed or VCC power is removed from the part.

ERASE (ERASE): The Erase (ERASE) instruction programs all bits in the specified memory location to the logical "1" state. The self-timed erase cycle starts once the ERASE instruction and address are decoded. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (TCS). A logic "1" at pin DO indicates that the selected memory location has been erased, and the part is ready for another instruction.

WRITE (WRITE): The Write (WRITE) instruction contains the 8 or 16 bits of data to be written into the specified memory location. The self-timed programming cycle, tWP, starts after the last bit of data is received at serial data input pin DI. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (TCS). A logic "0" at DO indicates that programming is still in progress. A logic "1" indicates that the memory location at the specified address has been written with the data pattern contained in the instruction and the part is ready for further instructions. A Ready/Busy status cannot be obtained if the CS is brought high after the end of the selftimed programming cycle, TWP.

ERASE ALL (ERAL): The Erase All (ERAL) instruction programs every bit in the memory array to the logic "1" state and is primarily used for testing purposes. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (TCS). The ERAL instruction is valid only at VCC = $5.0V \pm 10\%$.

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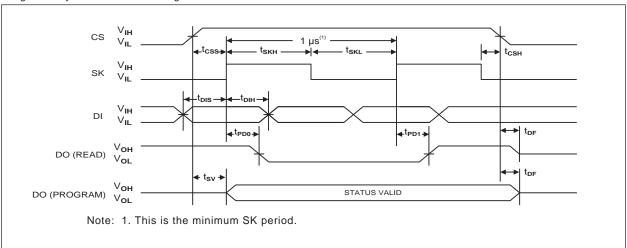
■ Function Descriptions

WRITE ALL (WRAL): The Write All (WRAL) instruction programs all memory locations with the data patterns specified in the instruction. The DO pin outputs the Ready/Busy status of the part if CS is brought high after being kept low for a minimum of 250 ns (TCS). The WRAL instruction is valid only at VCC = $5.0V \pm 10\%$.

ERASE/WRITE DISABLE (EWDS): To protect against accidental data disturb, the Erase/Write Disable (EWDS) instruction disables all programming modes and should be executed after all programming operations. The operation of the Read instruction is independent of both the EWEN and EWDS instructions and can be executed at any time.

■ Timing Diagrams

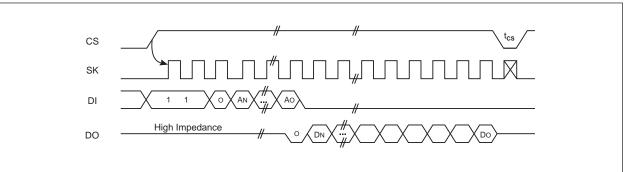
► Figure 1: Synchronous Data Timing



▶Table 3: Organization Key for Timing Diagram

I/O	K93C46(1K)		
170	X 16	X 8	
AN	A5	A6	
DN	D15	D7	

▶ Figure 2: READ Timing



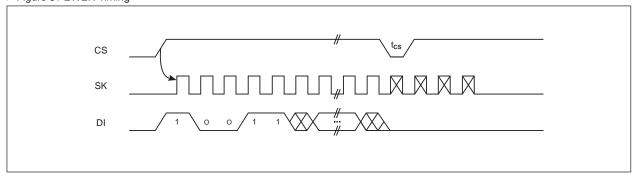
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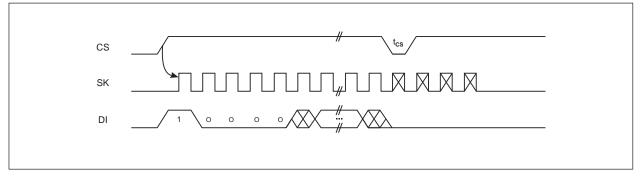
Three-wire Serial EEPROM 1K bits (128 X 8 or 64 X 16)

■ Timing Diagrams

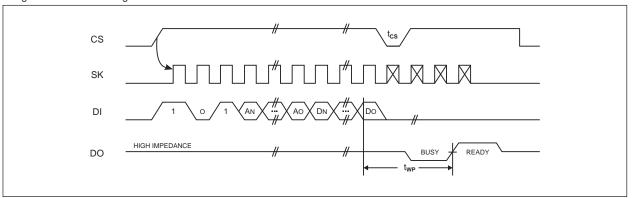
▶ Figure 3: EWEN Timing



▶ Figure 4: EWDS Timing



▶ Figure 5: WRITE Timing

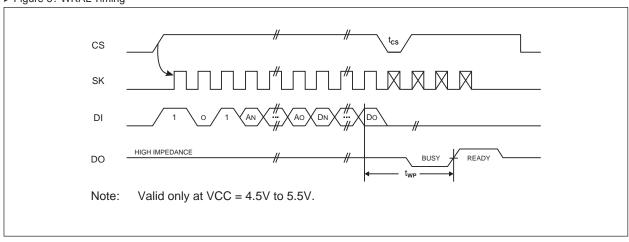


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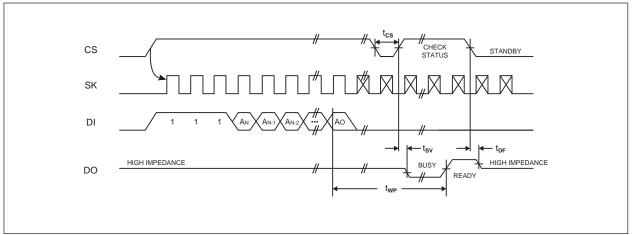
Three-wire Serial EEPROM 1K bits (128 X 8 or 64 X 16)

■ Timing Diagrams

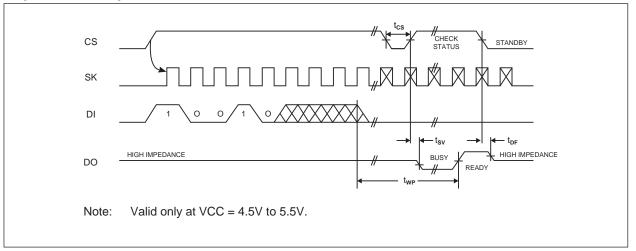
► Figure 6: WRAL Timing



▶ Figure 7: ERASE Timing



▶ Figure 8: ERAL Timing



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► Absolute Maximum Ratings

▶ Comments

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to this device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied or intended. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

■ DC Characteristics

► Applicable over recommended operating range from: TA = -40 C to +85 °C, VCC = + 1.8V to +5.5V, (unless otherwise noted)

Symbol	Parameter	Test Con	dition	Min	Тур	Max	Units
V _{CC1}	Supply Voltage	-		1.8	-	5.5	V
V _{CC2}	Supply Voltage	-		2.7	-	5.5	V
Vcc3	Supply Voltage	-		4.5	-	5.5	V
Icc	Supply Current	Vcc = 5.0V	Read at 1.0 MHz	-	0.5	2.0	mA
ICC	Supply Guilent	VCC = 3.0V	Write at 1.0 MHz	-	2	3.0	mA
I _{SB1}	Standby Current	Vcc = 1.8V	CS = 0V	-	-	1.0	μA
I _{SB2}	Standby Current	Vcc = 2.7V	CS = 0V	-	-	1.0	μA
I _{SB3}	Standby Current	Vcc = 5.0V	CS = 0V	-	-	1.0	μA
I _{IL(1)}	Input Leakage	Vin = 0V to Vcc		-	0.1	1.0	μA
I _{IL(2)}	Input Leakage	V _{IN} = 0V to Vcc		-	2.0	3.0	μA
loL	Output Leakage	VIN = 0V	to Vcc	-	0.1	1.0	μA
V _{IL1(3)}	Input Low Voltage	2.7V ≤ Vc	c < 5.5V	-0.3	-	0.8	
V _{IH1(3)}	Input High Voltage	2.7 V < VC	C < 0.5 V	2.0	-	Vcc + 0.3	V
$V_{\text{IL2(3)}}$	Input Low Voltage	1.8V ≤ Vc	o < 2.7\/	-0.5	-	Vcc + 0.3	
$V_{\text{IH2(3)}}$	Input High Voltage	1.00 < 00	∪ < 2.1 V	Vcc x 0.7	-	Vcc + 0.3	V
V _{OL1}	Output Low Voltage	2.7V ≤ Vcc ≤ 5.5V	IOL = 2.1mA	-	-	0.4	V
V _{OH1}	Output High Voltage	2.7 V < VCC < 3.5 V	IOH = -0.4mA	2.4	-		V
V _{OL2}	Output Low Voltage	1.8V ≤ Vcc ≤ 2.7V	IOL = 0.15mA	-	-	0.2	V
V_{OH2}	Output High Voltage	1.0V < VCC < 2.7V	$IOH = -100\mu A$	Vcc-0.2	-	-	V

Note: VIL min and VIH max are reference only and are not tested.

■ Pin Capacitance

► Applicable over recommended operating range from TA = 25°C, f = 1.0 MHz, VCC = +1.8V (unless otherwise noted)

Symbol	Test Conditions	Max	Unit	Conditions
COUT	Output Capacitance (DO)	5	pF	VOUT = 0V
CIN	Input Capacitance (CS, SK, DI, ORG)	5	pF	VIN = 0V

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■ AC Characteristics

► Applicable over recommended operating range from TA = -40° C to +85° C, VCC = + 1.8V to + 5.5V CL = 1 TTL Gate and 100pF (unless otherwise noted)

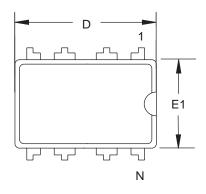
Symbol	Parameter	Test Co	ondition	Min	Тур	Max	Units
		4.5V ≤ V	/cc ≤ 5.5V	0		2	
fsк	SK Clock Frequency	2.7V ≤ V	/cc ≤ 5.5V	0	-	1	MHz
		1.8V ≤ V	cc ≤ 5.5V	0		0.25	
		4.5V ≤ V	cc ≤ 5.5V	250			
tsкн	SK High Time	2.7V ≤ V	cc ≤ 5.5V	250	-	-	ns
		1.8V ≤ V	cc ≤ 5.5V	1000			
		4.5V ≤ V	/cc ≤ 5.5V	250			
tskl	SK Low Time	2.7V ≤ V	/cc ≤ 5.5V	250	-	-	ns
		1.8V ≤ V	cc ≤ 5.5V	1000			
		4.5V ≤ V	cc ≤ 5.5V	250			
tcs	Minimum CS Low Time	2.7V ≤ V	cc ≤ 5.5V	250	-	-	ns
		1.8V ≤ V	cc ≤ 5.5V	1000			
			4.5V ≤ Vcc ≤ 5.5V	50			
tcss	CS Setup Time	Relative to SK	2.7V ≤ Vcc ≤ 5.5V	50	-	-	ns
			1.8V ≤ Vcc ≤ 5.5V	200			
			4.5V ≤ Vcc ≤ 5.5V	100			
tois	DI Setup Time	Relative to SK	2.7V ≤ Vcc ≤ 5.5V	100	-	-	ns
			1.8V ≤ Vcc ≤ 5.5V	400			
tсsн	CS Hold Time	Relative to SK		0	-	-	ns
			4.5V ≤ Vcc ≤ 5.5V	100			
tын	DI Hold Time	Relative to SK	2.7V ≤ Vcc ≤ 5.5V	100	-	-	ns
			1.8V ≤ Vcc ≤ 5.5V	400			
			4.5V ≤ Vcc ≤ 5.5V			250	
t _{PD1}	Output Delay to "1"	AC Test	2.7V ≤ Vcc ≤ 5.5V	-	-	250	ns
			1.8V ≤ Vcc ≤ 5.5V			1000	
			4.5V ≤ Vcc ≤ 5.5V			250	
t _{PD0}	Output Delay to "0"	AC Test	2.7V ≤ Vcc ≤ 5.5V	-	-	250	ns
			1.8V ≤ Vcc ≤ 5.5V			1000	
			4.5V ≤ Vcc ≤ 5.5V			250	
tsv	CS to Status Valid	AC Test	2.7V ≤ Vcc ≤ 5.5V	-	-	250	ns
			1.8V ≤ Vcc ≤ 5.5V			1000	
	CS to DO in High	AC Test	4.5V ≤ Vcc ≤ 5.5V			100	
tof	Impedance	CS = VIL	2.7V ≤ Vcc ≤ 5.5V	-	-	100	ns
	impodanoe	33 - 112	1.8V ≤ Vcc ≤ 5.5V			400	
twp	Write Cycle Time	-	-	-	1.5	5	ms
Endurance ⁽¹⁾	5.0V, 25°C		-	1M	-	-	Write Cycle

Note: 1. This parameter is characterized and is not 100% tested.

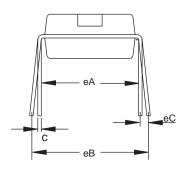
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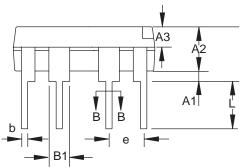
■ 8-lead PDIP package diagram



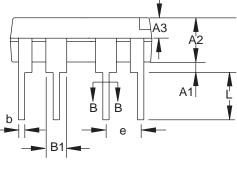
Top View



End View



Side View



Base Metal With Plating

Section B-B

COMMON DIMENSIONS

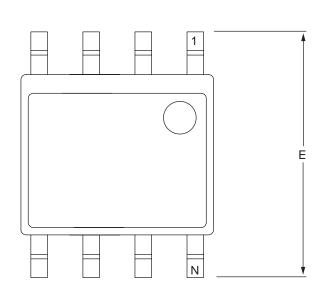
(Unit of Measure = mm)

SYMBOL	MIN	MAX		
Α	3.60	4.00		
A1	0.51	-		
A2	3.10	3.50		
А3	1.50	1.70		
b	0.44	0.53		
b1	0.43	0.48		
В	1.52 BSC			
С	0.25	0.31		
c1	0.24	0.26		
D	9.05 9.45			
E1	6.15	6.55		
е	2.54	BSC		
eA	7.62 BSC			
eB	7.62	9.50		
eC	0	0.94		
L	3.00	-		

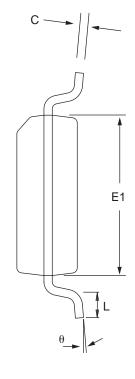
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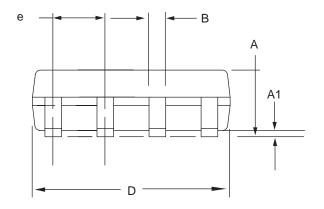
■ 8-lead SOP package diagram



Top View



End View



Side View

COMMON DIMENSIONS

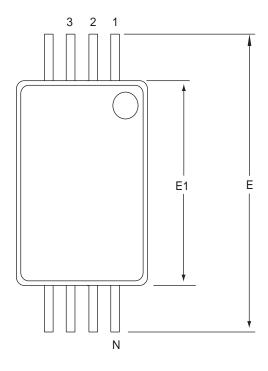
(Unit of Measure = mm)

SYMBOL	MIN	MAX		
Α	1.35	1.75		
A1	0.10	0.25		
b	0.31	0.51		
С	0.17	0.25		
D	4.70	5.10		
E1	3.80	4.00		
E	5.79	6.20		
е	1.27 BSC			
L	0.40	1.27		
θ	0°	8°		

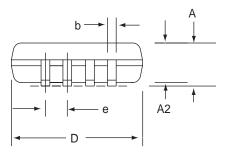
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Three-wire Serial EEPROM 1K bits (128 X 8 or 64 X 16)

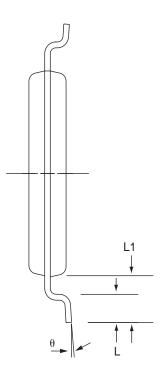
■ 8-lead TSSOP package diagram



Top View



Side View



End View

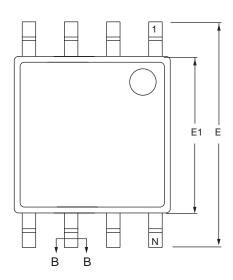
COMMON DIMENSIONS

(Unit of Measure = mm)

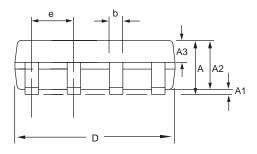
	-		
SYMBOL	MIN	MAX	
D	2.80	3.20	
Е	6.20	6.60	
E1	4.20	4.60	
А	-	1.20	
A2	0.80 1.15		
b	0.19 0.30		
е	0.65	BSC	
L	0.45	0.75	
L1	1.00 BSC		
θ	0°	8°	

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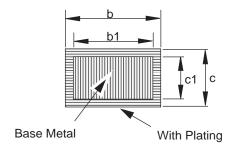
■ 8-lead MSOP package diagram



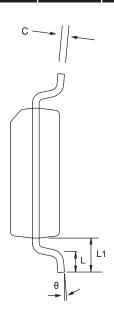
Top View



Side View



Section B-B



End View

COMMON DIMENSIONS

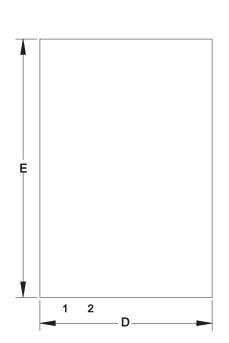
(Unit of Measure = mm)

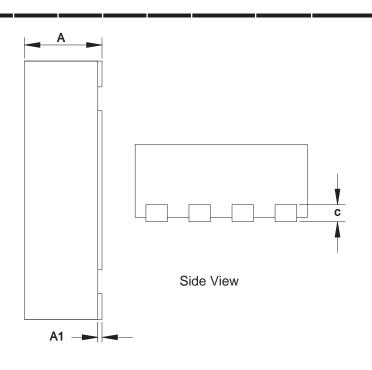
SYMBOL	MIN	MAX		
А	-	1.10		
A1	0.05	0.15		
A2	0.75	0.95		
A3	0.30	0.40		
b	0.29	0.38		
b1	0.28 0.33			
С	0.15	0.20		
c1	0.14	0.16		
D	2.90	3.10		
Е	4.70	5.10		
E1	2.90	3.10		
е	0.65 BSC			
L	0.40	0.70		
L1	0.95 BSC			
θ	0°	8°		

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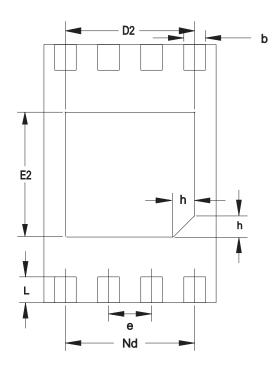
■ 8-pad DFN package diagram





Top View

End View



COMMON DIMENSIONS (Unit of Measure = mm)

SYMBOL	MIN	MAX		
Α	0.70	0.80		
A1	-	0.05		
b	0.18	0.30		
С	0.18	0.25		
D	1.90	2.10		
D2	1.50 REF			
е	0.50 BSC			
Nd	1.50	BSC		
E	2.90	3.10		
E2	1.60 BSC			
L	0.30	0.50		
h	0.20	0.30		

Bottom View

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■ Ordering Information

Code Number

Part Number Κ 93 XXX Χ Χ $X \quad X \quad X \quad X$ 1 2 3 4 5 6 7 8 9

1.Prefix

2.Series Name

93: Three-wire (SPI) Interface

C46 = 1K bits

3.EEPROM Density

D = PDIP S = SOP T = TSSOP

M = MSOPN = DFN

4.Design Option Version code 5.Package Type 6.Temperature Range

I = Industry (-40 °C to 85 °C)

7.Pack Type

T = Tube

R = Tape & Reel

8.Plating Technology

Blank = Standard SnPb plating

G = RoHS compliant

S = Green, level 1

X = Green, level 3

9.Operating Voltage

A = 1.8 to 5.5 V

Available package types

Model	PDIP	SOP	TSSOP	MSOP	DFN
K93C46	\checkmark	\checkmark	\checkmark	V	V

■ Product Datasheet Change Notice

Datasheet Revision History		
Version	Content	Date
1.1	Initial version	Jul., 2008
1.2	Package information update	Jan., 2011

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Three-wire Serial EEPROM



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K93C Series (SPI Bus) Serial EEPROM Data Sheet, Revision 1.2

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